Schottky Barrier Diode

unit

SB10-03A2/SB10-03A3

30V, 1.0A Rectifier

Applications

• High frequency rectification (switching regulators, converters, choppers).

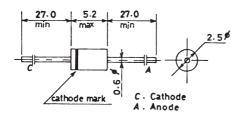
Features

- Low forward voltage (V_F max=0.55V).
- Fast reverse recovery time (t_{rr} max=30ns).
- Low switching noise.
- Average rectified current (Io=1.0A).

Absolute Maximum Ratings at Ta=25°C

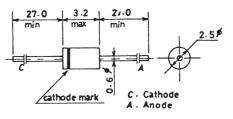
Repetitive Peak Reverse Voltage	V _{RRM}			30	V	
Nonrepetitive Peak Reverse	V _{RSM}			35	V	
Surge Voltage			-			
Average Rectified Current	Io	SB10-03A2		1.0	А	
		50Hz, resistive load, sine wave,	Ta=50°C			
		(L=8mm, 10×10mm ² print land)				
		SB10-03A3		1.0	А	
		50Hz, resistive load, sine wave,	Ta=46°C			
		(L=3mm, 5×5mm ² print land)				
Surge Forward Current	I _{FSM}	50Hz sine wave, 1 cycle		40	А	
Junction Temperature	Tj			125	°C	
Storage Temperature	Tstg		-40 to	+125	°C	
Electrical Characteristics at Ta=25°C min			min	typ	max	unit
Forward Voltage	/ _F	I _F =1.0A		• •	0.55	V
Reverse Current I	R	V _R =30V			1.0	mA
Reverse Recovery Time t ₁	rr	I _{FM} =1A, -di/dt=50A/µs			30	ns
Thermal Resistance	Rth(j-a)	No fin, device only			140	°C/W
(Junction-Ambient)						

[SB10-03A2] Package Dimensions 1208 (unit : mm)



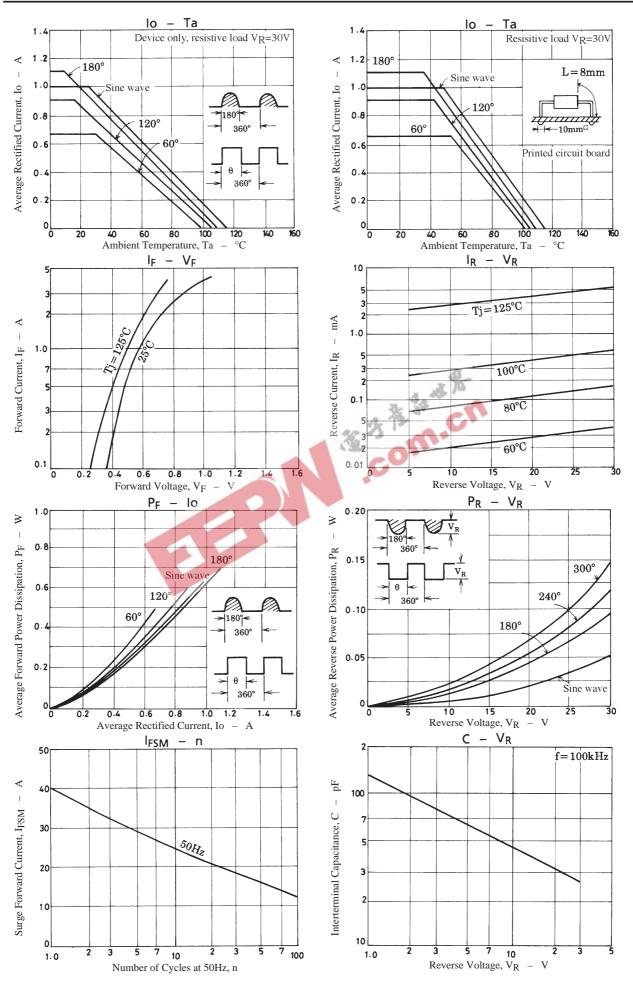
[SB10-03A3] Package Dimensions 1209



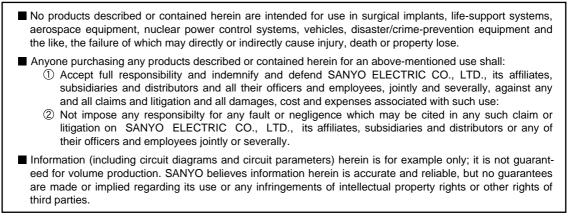


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This catalog provides information as of October, 1997. Specifications and information herein are subject to change without notice.